

AMENDMENTS TO THE CLAIMS

1. (Original) A method of forming storage nodes in a dynamic random access memory (DRAM) on a semiconductor wafer, the semiconductor wafer comprising a substrate, a thin film layer positioned on the substrate, and a photoresist layer positioned on the thin film layer, the method comprising:
- performing a first exposure process to form first exposure regions that are linear and parallel with each other on the photoresist layer;
- performing a second exposure process to form second exposure regions that are interlaced with and perpendicular to each other on the photoresist layer;
- performing a development process on the first exposure regions and the second exposure regions of the photoresist layer;
- removing the first exposure regions and the second exposure regions of the photoresist layer to form an array photoresist layer on the thin film layer; and
- using the array photoresist layer as a mask to perform an etching process to remove portions of the thin film layer not covered by the array photoresist layer so as to form an array thin film layer, the array thin film layer being used as the storage nodes in the DRAM.
1. (Previously amended) A method of forming storage nodes in a dynamic random access memory (DRAM) on a semiconductor wafer, the semiconductor wafer comprising a substrate, a thin film layer positioned on the substrate, and a photoresist layer positioned on the thin film layer, the method comprising:
- performing a first exposure process to form first exposure regions including a plurality of lines that are parallel to each other and covering each storage node;

performing a second exposure process to form second exposure regions cutting the plurality of lines of the first exposure regions;

performing a development process on the first exposure regions
5 and the second exposure regions of the photoresist layer;

removing the first exposure regions and the second exposure regions of the photoresist layer to form an array photoresist layer on the thin film layer; and

using the array photoresist layer as a mask to perform an
10 etching process to remove portions of the thin film layer not covered by the array photoresist layer so as to form an array thin film layer, the array thin film layer being used as the storage nodes in the DRAM.

15 1. (Currently amended) A method of forming storage nodes in a dynamic random access memory (DRAM) on a semiconductor wafer, the semiconductor wafer comprising a substrate, a thin film layer positioned on the substrate, and a photoresist layer positioned on the thin film layer, the method comprising:

20 performing a first exposure process to form first exposure regions that are lines parallel with each other on the photoresist layer;

performing a second exposure process to form second exposure regions that are rectangles interlaced with and perpendicular to each other on the photoresist layer, and the second exposure
25 regions doing not overlap the first exposure regions;

performing a development process on the first exposure regions and the second exposure regions of the photoresist layer;

removing the first exposure regions and the second exposure regions of the photoresist layer to form an array photoresist layer
30 on the thin film layer; and

using the array photoresist layer as a mask to perform an etching process to remove portions of the thin film layer not

covered by the array photoresist layer so as to form an array thin film layer, the array thin film layer being used as the storage nodes in the DRAM.